

Transistor

**Panasonic**

# 2SC2631

Silicon NPN epitaxial planer type

For low-frequency high breakdown voltage amplification

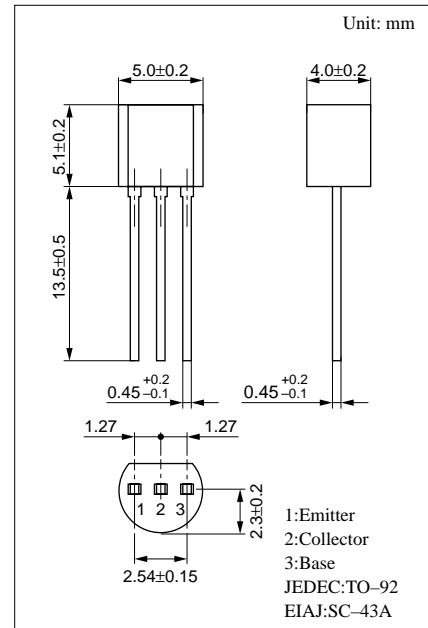
Complementary to 2SA1123

## Features

- Satisfactory linearity of forward current transfer ratio  $h_{FE}$ .
- High collector to emitter voltage  $V_{CEO}$ .
- Small collector output capacitance  $C_{ob}$ .

## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	150	V
Collector to emitter voltage	$V_{CEO}$	150	V
Emitter to base voltage	$V_{EBO}$	5	V
Peak collector current	$I_{CP}$	100	mA
Collector current	$I_C$	50	mA
Collector power dissipation	$P_C$	750	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C



## Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 100V, I_E = 0$			1	$\mu A$
Collector to emitter voltage	$V_{CEO}$	$I_C = 0.1mA, I_B = 0$	150			V
Emitter to base voltage	$V_{EBO}$	$I_E = 10\mu A, I_C = 0$	5			V
Forward current transfer ratio	$h_{FE}^*$	$V_{CE} = 5V, I_C = 10mA$	130		330	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 30mA, I_B = 3mA$			1	V
Transition frequency	$f_T$	$V_{CB} = 10V, I_E = -10mA, f = 200MHz$		160		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$			3	pF
Noise voltage	NV	$V_{CE} = 10V, I_C = 1mA, G_V = 80dB$ $R_g = 100k\Omega, \text{Function} = \text{FLAT}$		150	300	mV

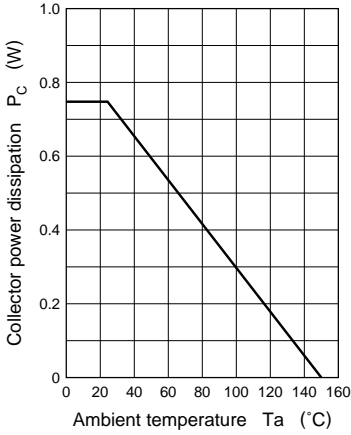
\* $h_{FE}$  Rank classification

Rank	R	S
$h_{FE}$	130 ~ 220	185 ~ 330

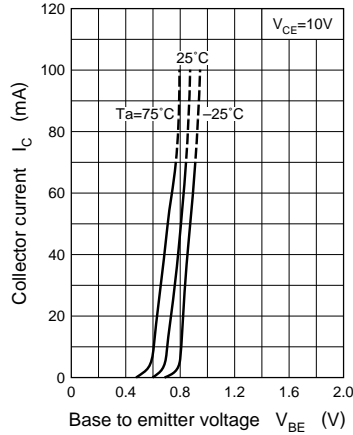
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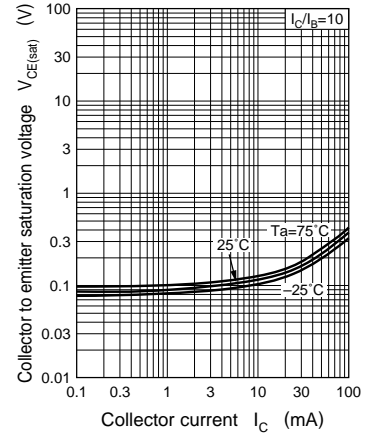
$P_C - T_a$



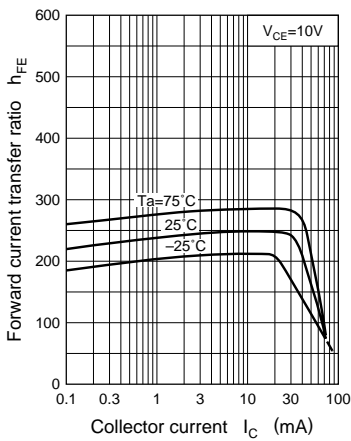
$I_C - V_{BE}$



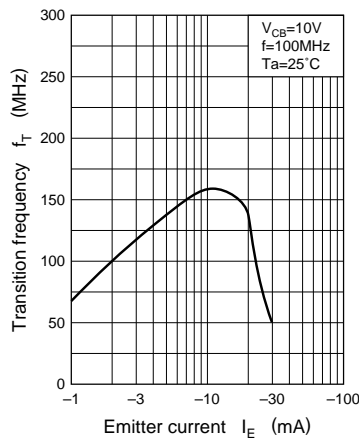
$V_{CE(sat)} - I_C$



$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$

